



Insulated Gate Bipolar Transistors IGBT-Chips

"S" series with improved SCSOA capability

	Type $T_{vj} = 150^{\circ}\text{C}$	V_{CES}	$V_{CE(sat)}$	β_{AV}	C_{es} typ	t_r typ. 25°C	Chip type	Chip size dimensions		Source G bond wire pitch/mm	Equivalent device equivalent	Dim. out- line No.
		V	V	A	pF	ns		mm	mil			
Low V _{CE(sat)}	IXSD10N60	600	2.5	10	750	300	IX32	4.39 x 3.60	173 x 142	12 mil x 1	IXSH10N60	3
	IXSD16N60		2.3	16	920	310	IX3T	4.39 x 3.60	173 x 142	12 mil x 1 ②	IXSH16N60	6
	IXSD24N60		2	20	1800	500	IX43	5.64 x 4.67	222 x 184	15 mil x 1	IXSH24N60	1
	IXSD30N60		2.3	20	2760	400	IX5T	6.73 x 6.61	265 x 260	10 mil x 4	IXSH30N60	8
	IXSD40N60		2.2	20	4500	400	IX7Z	8.88 x 7.16	350 x 282	12 mil x 4	IXSH40N60	10
	IXSD25N100	1000	3.4	20	2850	1200	IX5T	6.73 x 6.61	265 x 260	10 mil x 4	IXSH25N100	8
IXSD45N100		2.3	20	4150	1000	IX7M	8.91 x 7.22	351 x 284	12 mil x 4	IXSH45N100	9	
IXSD45N120	1200	2.4	20	4150	1000	IX7M	8.91 x 7.22	351 x 284	12 mil x 4	IXSH45N120	9	
High Speed	IXSD10N60A	600	3	10	750	175	IX32	4.39 x 3.60	173 x 142	12 mil x 1	IXSH10N60A	3
	IXSD24N60A		2.6	20	1800	275	IX43	5.64 x 4.67	222 x 184	15 mil x 1	IXSH24N60A	1
	IXSD30N60A		2.7	20	2760	200	IX5T	6.73 x 6.61	265 x 260	10 mil x 4	IXSH30N60A	8
	IXSD40N60A		2.6	20	4500	200	IX7Z	8.88 x 7.16	350 x 282	12 mil x 4	IXSH40N60A	10
	IXSD50N60A		2.4	20	4500	400	IX7Z	8.88 x 7.16	350 x 282	12 mil x 4	IXSK50N60AU1	10
	IXSD25N100A	1000	3.9	20	2850	800	IX5T	6.73 x 6.61	265 x 260	10 mil x 4	IXSH25N100A	8
	IXSD35N100A		3.2	20	4400	700	IX7M	8.91 x 7.22	351 x 284	12 mil x 4	IXSH35N100A	9
	IXSD10N120A	1200	4	10	800	620	IX3T	4.39 x 3.60	173 x 142	12 mil x 1 ②	IXSH10N60A	6
	IXSD15N120A		4	15	1800	600	IX4T	5.77 x 4.96	227 x 195	15 mil x 1	IXSH15N60A	7
	IXSD25N120A		3.9	20	2850	650	IX5T	6.73 x 6.61	265 x 260	10 mil x 4	IXSH25N60A	8
IXSD35N120A		3.6	20	3750	500	IX7M	8.91 x 7.22	351 x 284	12 mil x 4	IXSH35N120A	9	
IXSD35N135A	1350	3.6	20	4150	400	IX7M	8.91 x 7.22	351 x 284	12 mil x 4	IXSH35N135A	9	

① Recommended Gate bond wire is 8 mil resp. 6 mil at ② types.

IXYS reserves the right to change limits, test conditions and dimensions.